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JOURNAL PUBLICATION

1. **N.Anbuselvan** P.Anandan “Breakdown Voltage Analysis in Quaternary InAlGaN HEMT of High-K Passivation Layer for High Power Applications” Accepted in Journal of Computational and Theoretical Nanoscience Vol. 17, 1–5, (2020).
2. **N.Anbuselvan** P.Anandan A.Manju “Model of $\text{HfO}_2/\text{Al}_2\text{O}_3$ Dielectric AlN/InN/AlGaN MOS HEMT for Power Application”, International Journal of Innovative Technology and Exploring Engineering (IJITEE) ISSN: 2278-3075, Volume-9 Issue-1, November, (2019)
3. **N.Anbuselvan**, N. Mohankumar, A. Mohanbabu “Analytical noise characterization of quaternary AlInGaN HEMTs "Journal of Nano Electronics and Optoelectronics, volume 14,No.2 pp 247-254. (2019) (**Impact factor: 1.069**).
4. **N.Anbuselvan**, Mohankumar N & Mohanbabu A, “Analytical modeling of 2DEG with 2DHG Polarization Charge density drain current and Small-signal model of Quaternary AlInGaN HEMTs”, International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, Wiley publication doi:10.1002/jnm.2609 (2019) (**Impact factor : 0.8**).
5. **N. Anbuselvan**, P. Amudhalakshmi, N. Mohankumar “Analytical modeling of 2DEG and 2DHG charge balancing in quaternary $\text{Al}_{0.42}\text{In}_{0.03}\text{Ga}_{0.55}\text{N}/\text{Al}_{0.3}\text{In}_{0.7}\text{N}$ HEMTs:” Journal of Computational Electronics Volume 17, issue 3, Pages 1191-1198, Springer publication (2018) (**Impact factor: 1.526**).
6. N.Mohankumar, A.Mohanbabu, S.Baskaran, P.Anandan, **N.Anbuselvan** and P.Bharathivikkriman “Modeling of Sheet Carrier Density, DC and Transconductance of Novel $\text{In}_x\text{Al}_{1-x}\text{N}/\text{GaN}$ -Based HEMT Structures” Advanced Materials Research Vol. 1105 pp 99-104. (2015) (**Impact factor: 0.23**).
7. Theodore Chandra S, Balamurugan NB,Bhuvaneswari M, **Anbuselvan N** & Mohankumar N “Analysis of Charge Density and Femi Level of AlInSb/InSb Single Gate High Electron Mobility Transistor”, Journal of Semiconductor, vol.36, no.6,pp.0640031-0640036 (2015). (**Impact factor: 0.50**).
8. A.Mohanbabu, **N.Anbuselvan**, N.Mohankumar, Godwin Raj, Chandan Kumar Sarkar “Modeling of Sheet carrier density and Microwave frequency characteristics in Spacer based AlGaN/AlN/GaN HEMT Devices”, Journal of Solid State Electronics, Volume 91 pages 44–52 (2014). (**Impact factor: 1.514**).

9. S.Baskaran, A.Mohanbabu, **N.Anbuselvan**, N.Mohankumar, Godwin Raj, Chandan Kumar Sarkar “Modeling of Sheet carrier density and DC characteristics in Spacer based AlGa_N/AlN/GaN HEMT Devices”, Journal of Super lattices and microstructures, Volume 64 pages 470–482 (2013). (**Impact factor: 1.979**).